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Kind regards,

Team Nexperia

Product data sheet

1. Product profile

1.1 General description

Single high-voltage switching diode, encapsulated in a SOD123F small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Small and flat lead SMD plastic package
- Reverse voltage: V_R ≤ 200 V

1.3 Applications

General-purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		<u>[1]</u> -	-	200	mA
V_R	reverse voltage		-	-	200	V
t _{rr}	reverse recovery time		[2] _	-	50	ns

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.



^[2] When switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 3 mA.

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Single high-voltage switching diode

Pinning information 2.

Table 2. **Pinning**

Pin	Description	Simplified outline	Symbol
1	cathode	<u>[1]</u>	
2	anode	1 2	1 🔁 2
			sym001

^[1] The marking bar indicates the cathode.

Ordering information 3.

Ordering information Table 3.

Type number	Package		
	Name	Description	Version
BAS21H	-	plastic surface-mounted package; 2 leads	SOD123F

Marking

Product data sheet

Table 4. **Marking codes**

Type number	Marking code
BAS21H	B2

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Single high-voltage switching diode

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Limiting values 5.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •	-		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	250	V
V_R	reverse voltage		-	200	V
I _F	forward current		<u>[1]</u> _	200	mA
I _{FRM}	repetitive peak forward current	t_p = 1 ms; δ = 0.25	-	625	mA
I _{FSM}	non-repetitive peak forward current	square wave	[2]		
		$t_p = 1 \mu s$	-	9	Α
		$t_p = 100 \; \mu s$	-	3	Α
		$t_p = 10 \text{ ms}$	-	1.7	А
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3] _	375	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

Thermal characteristics

Product data sheet

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2] -	-	330	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[3] -	-	70	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] $T_i = 25$ °C prior to surge.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

^[2] Reflow soldering is the only recommended soldering method.

Soldering point of cathode tab.

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BAS21H

Single high-voltage switching diode

7. Characteristics

Table 7. Characteristics

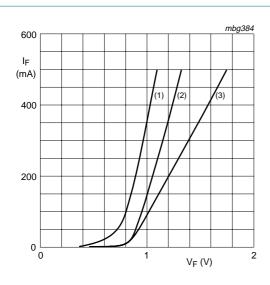
 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

arrib							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{F}	/ _F forward voltage	$I_F = 100 \text{ mA}$	<u>[1]</u>	-	-	1	V
		I _F = 200 mA	<u>[1]</u>	-	-	1.25	V
I _R	reverse current	V _R = 200 V		-	-	100	nA
	V _R = 200 V; T _j = 150 °C		-	-	100	μΑ	
C _d	diode capacitance	$V_R = 0 V$; $f = 1 MHz$		-	-	5	pF
t _{rr}	reverse recovery time		[2]	-	-	50	ns

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

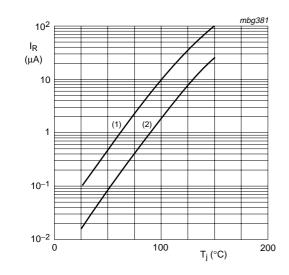
^[2] When switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω ; measured at I_R = 3 mA.

Single high-voltage switching diode



- (1) $T_{amb} = 150 \,^{\circ}C$; typical values
- (2) $T_{amb} = 25 \,^{\circ}C$; typical values
- (3) $T_{amb} = 25 \,^{\circ}C$; maximum values

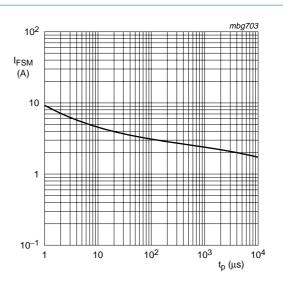
Fig 1. Forward current as a function of forward voltage



- (1) $V_R = V_{Rmax}$; maximum values
- (2) $V_R = V_{Rmax}$; typical values

Product data sheet

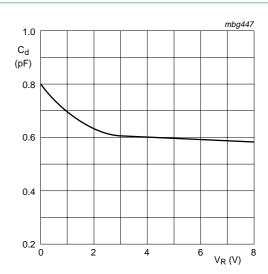
Fig 3. Reverse current as a function of junction temperature



Based on square wave currents.

 $T_i = 25$ °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



 $f = 1 \text{ MHz}; T_{amb} = 25 \, ^{\circ}\text{C}$

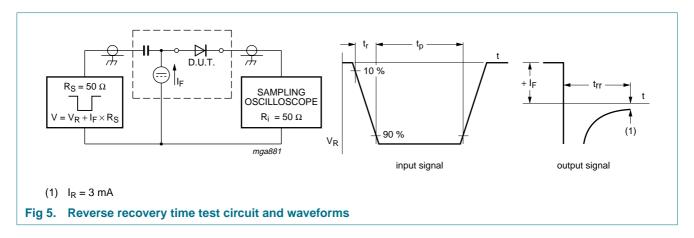
Fig 4. Diode capacitance as a function of reverse voltage; typical values

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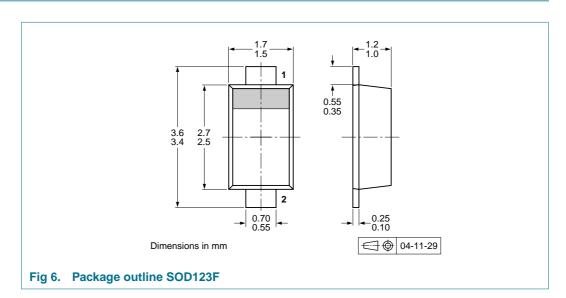
NXP Semiconductors BAS21H

Single high-voltage switching diode

8. Test information



9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

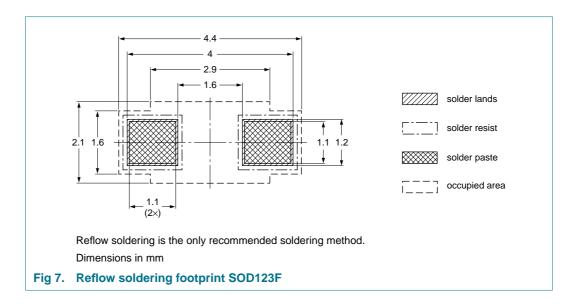
Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
BAS21H	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135	

^[1] For further information and the availability of packing methods, see <u>Section 15</u>.

Single high-voltage switching diode

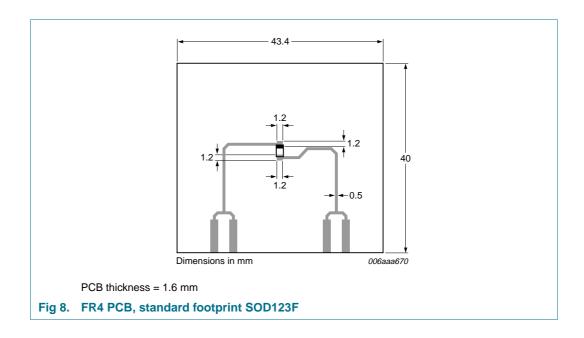
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11. Soldering



12. Mounting

Product data sheet



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13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BAS21H_2	20061103	Product data sheet	-	BAS21H_1			
Modifications:		of this data sheet has beer f NXP Semiconductors.	n redesigned to comply w	vith the new identity			
	 Legal texts have been adapted to the new company name where appropriate. 						
	Section 1.1 "General description": amended						
	 Table 1 "Quick reference data": I_F forward current table note added 						
	 <u>Table 5 "Limiting values"</u>: I_F forward current table note added 						
	 <u>Table 5 "Limiting values"</u>: I_{FRM} repetitive peak forward current condition amended 						
	Table 5 "Limiting values": I _{FSM} non-repetitive peak forward current condition amended						
	Table 6: R _{th(i-sp)} thermal resistance from junction to solder point table note added						
	Table 7 "Characteristics": V _F forward voltage unit amended						
	Figure 2: figure title and figure note amended						
	• Figure 3: amended						
	Section 12 "Mounting": added						
	Section 14.4	4 "Trademarks": added					
BAS21H_1	20050411	Product data sheet	-	-			

Single high-voltage switching diode

14. Legal information

14.1 **Data sheet status**

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions
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